

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	8223935	@ad>"19991222" @rlad>"19991222" @pt1d>"19991222"	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:15
L4	1753	okudaira.in. not L3	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:15
L5	125	4 and mitsubishi.es.	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:15
L6	55	capacitor and 5	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:16
L7	8	oxygen and 6	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:16
L8	1	1999-414765.NRAN.	DERWENT	OR	ON	2006/06/01 15:23
L9	2	("6078072").PN:	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/01 15:32
L10	2	9 and metal adj layer	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/01 15:32
S1	2	("6750092").PN:	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/31 11:41
S2	8218970	@ad>"19991222" @rlad>"19991222" @pt1d>"19991222"	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 11:42
S4	29	("20010006838" "20010031527" "20010054730" "20020055254" "20020058415" "20020146513" "2002192896" "5231056" "5314845" "5372849" "5834357" "6063705" "6420582" "6440495" "6479100").PN	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:34
S5	9	S4 not S2	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:03
S6	359928	(\$5ruther\$ ru).not S2	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:04
S7	5	S5 and S6	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:07
S8	548185	(oxygen:"0.sub.2") not S2	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:07
S9	4	S7 and S8	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:12
S10	28	((cvd chemical adj vapor) with S6 with S8) not S2	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:19
S11	181356	samsung.as.	US_PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:19

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S12	28	S10 not S11	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:22
S13	27	oxide and S12	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:23
S14	2652	electrode with ((oxygen "0. _{sub} .2") near concentration) not S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 16:33
S15	8681	438/239,652,658,660,679,680,681,686,124,250.ccls. 257/e21.008,e21.011.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 12:52
S16	8	S14 with S6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:06
S17	6	(S14 and S15) not (S5 S10 S11 S16 S2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 13:28
S18	0	S6 with ((oxygen "0. _{sub} .2") near concentration) and S15 not (S2 S5 S10 S11 S16 S17)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 16:20
S21	4208174	(iridium ir,rhodium rh platinum pt osmium os palladium pd) not S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 16:29
S22	3536	S21 with electrode with S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 16:31
S23	428	capacitor and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 16:33
S25	582859	(oxygen "0. _{sub} .2") not S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 16:33
S26	2701	electrode with ((oxygen "0. _{sub} .2") near concentration) not S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 16:33
S27	29	(S21 with S26) and capacitor and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 17:19
S28	34	(S6 with "0. _{sub} .2" with electrode) not S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 17:21
S29	19	S28 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/31 17:21
S30	10	(US-20020192896-\$ or US-20010006838-\$ or US-20010050391-\$).dld. or (US-6420582-\$ or US-6403441-\$ or US-6187622-\$ or US-6156599-\$ or US-5852307-\$ or US-6078072-\$ or US-6333529-\$).dld.	US-PGPUB; USPAT	OR	ON	2006/05/31 17:37
S31	0	(method and assembling and plurality and semiconductor adj chips and comprising and steps and providing and portion and wafer and containing and contact adj pattern adj area and dielectric and without adj portion and bonding adj pads and outer adj periphery and wire adj bonding and encapsulant and cutting).clm.	US-PGPUB	OR	ON	2006/05/31 19:04